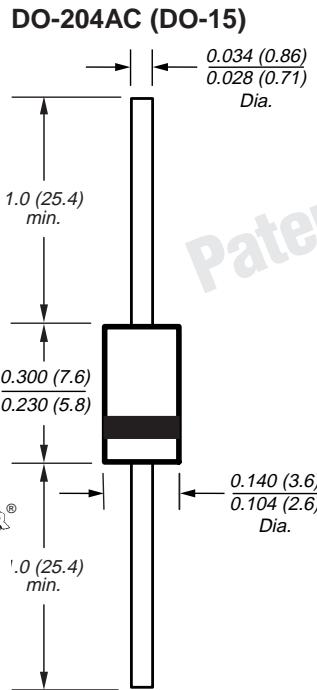




Miniature High Voltage Glass Passivated Rectifier

 Reverse Voltage 1200 to 1600 V
 Forward Current 1.0 A

SUPERRECTIFIER®

* Glass-plastic encapsulation technique is covered by Patent No. 3,996,602 and brazed-lead assembly by Patent No. 3,930,306.

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0.
- High temperature metallurgically bonded construction
- Cavity-free glass passivated junction
- 1.0 ampere operation at TA=75°C with no thermal runaway
- Typical IR less than 0.1µA
- Hermetically sealed package
- Capable of meeting environmental standards of MIL-S-19500
- High temperature soldering guaranteed: 350°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

Mechanical Data

Case: JEDEC DO-204AC, molded plastic over glass body

Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.015 oz., 0.4 g

Maximum Ratings & Thermal Characteristics

 Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	GI1-1200GP	GI1-1400GP	GI1-1600GP	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	1200	1400	1600	V
Maximum RMS voltage	V _{RMS}	840	980	1120	V
Maximum DC blocking voltage	V _{DC}	1200	1400	1600	V
Maximum average forward rectified current 0.375" (9.5mm) lead length at TA=75°C	I _{F(AV)}		1.0		A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}		30		A
Typical thermal resistance ⁽¹⁾	R _{θJA}		55		°C/W
Operating junction and storage temperature range	T _{J,TSTG}		-65 to +175		°C

Electrical Characteristics

 Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	GI1-1200GP	GI1-1400GP	GI1-1600GP	Unit
Maximum instantaneous forward voltage at 1.0A at 3.14A	V _F	1.1 1.3			V
Maximum DC reverse current TA= 25°C at rated DC blocking voltage TA=100°C	I _R	10 100			µA
Maximum reverse recovery time at I _{FM} =20mA, I _{RM} =2mA	t _{rr}		25		µs
Maximum reverse recovery time typical at I _F =0.5A, I _R =1.0A, I _{rr} =0.25A maximum	t _{rr}		0.7 1.5		µs
Maximum forward recovery time at I _{FM} =20mA	t _{frr}		1.0		µs
Typical junction capacitance at 4.0V, 1MHz	C _J		15		pF

Notes: (1) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted

GI1-1200GP thru GI1-1600GP



Vishay Semiconductors
formerly General Semiconductor

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Forward Current Derating Curve

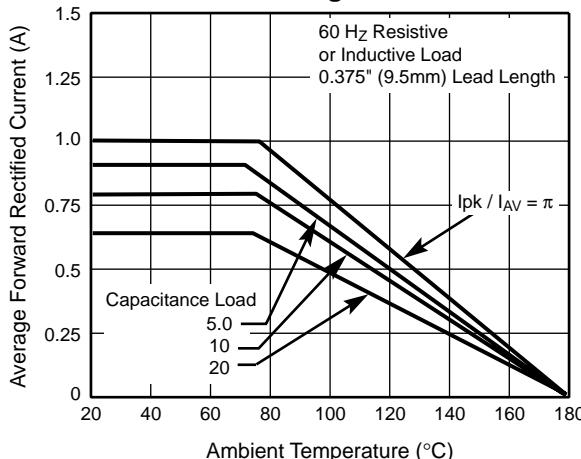


Fig. 2 – Maximum Non-Repetitive Peak Forward Surge Current

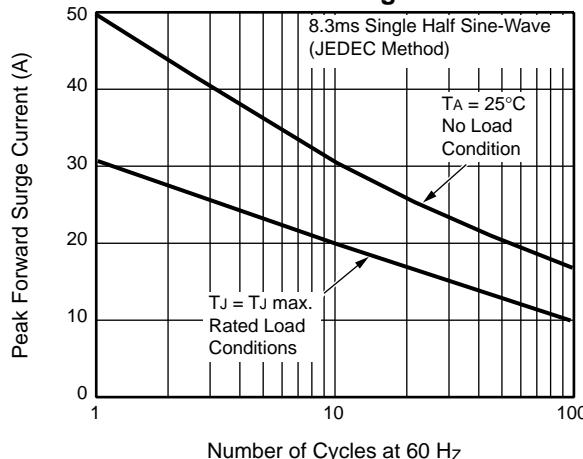


Fig. 3 – Typical Instantaneous Forward Characteristics

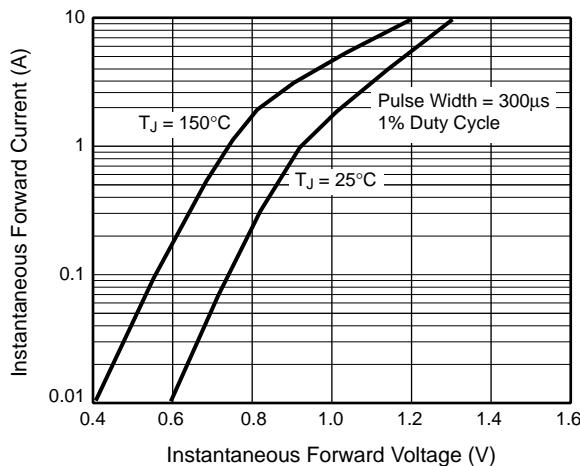


Fig. 4 – Typical Reverse Characteristics

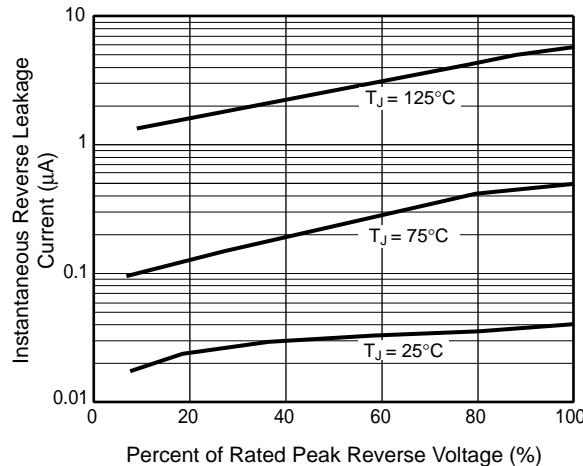


Fig. 5 – Typical Junction Capacitance

